

Description

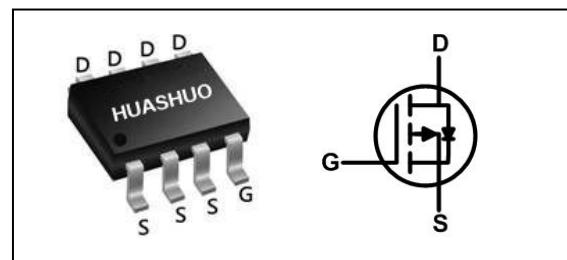
The HSM6117 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The HSM6117 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Product Summary

V _{DS}	-60	V
R _{DSON,max}	14	mΩ
I _D	-15	A

SOP-8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-60	V
V _{GS}	Gate-Source Voltage	± 20	V
I _D @T _C =25°C	Continuous Drain Current, -V _{GS} @ -10V ¹	-15	A
I _D @T _C =100°C	Continuous Drain Current, -V _{GS} @ -10V ¹	-9.5	A
I _{DM}	Pulsed Drain Current ²	-60	A
I _{AS}	Avalanche Current	40	A
P _D @T _C =25°C	Total Power Dissipation ⁴	5.2	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient ¹	---	85	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	24	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-60	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-10A	---	12	14	mΩ
		V _{GS} =-4.5V , I _D =-8A	---	14	17	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.0	-1.7	-2.5	V
△V _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	4.28	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-48V , V _{GS} =0V , T _J =25°C	---	---	1	uA
		V _{DS} =-48V , V _{GS} =0V , T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ± 20V , V _{DS} =0V	---	---	± 100	nA
g _{fs}	Forward Transconductance	V _{DS} =-10V , I _D =-10A	---	43	---	S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	2.6	---	Ω
Q _g	Total Gate Charge	V _{DS} =-30V , V _{GS} =-10V , I _D =-5A	---	85	---	nC
Q _{gs}	Gate-Source Charge		---	11	---	
Q _{gd}	Gate-Drain Charge		---	30	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-30V , V _{GS} =-10V , R _G =6Ω, I _D =-1A	---	18	---	ns
T _r	Rise Time		---	12	---	
T _{d(off)}	Turn-Off Delay Time		---	100	---	
T _f	Fall Time		---	68	---	
C _{iss}	Input Capacitance	V _{DS} =-30V , V _{GS} =0V , f=1MHz	---	4635	---	pF
C _{oss}	Output Capacitance		---	524	---	
C _{rss}	Reverse Transfer Capacitance		---	241	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _s	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current	---	---	-15	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _s =-1A , T _J =25°C	---	---	-1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=-30V,V_{GS}=-10V,L=0.5mH,I_{AS}=-40A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

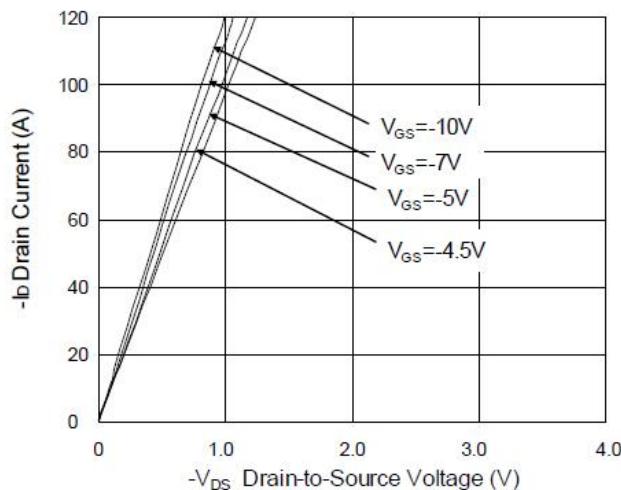


Fig.1 Typical Output Characteristics

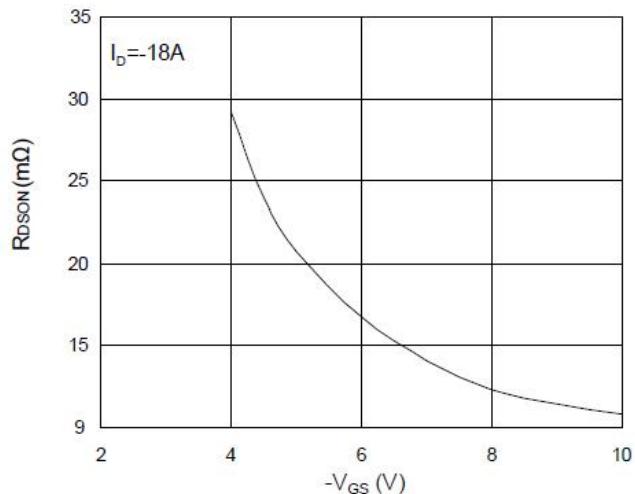


Fig.2 On-Resistance vs G-S Voltage

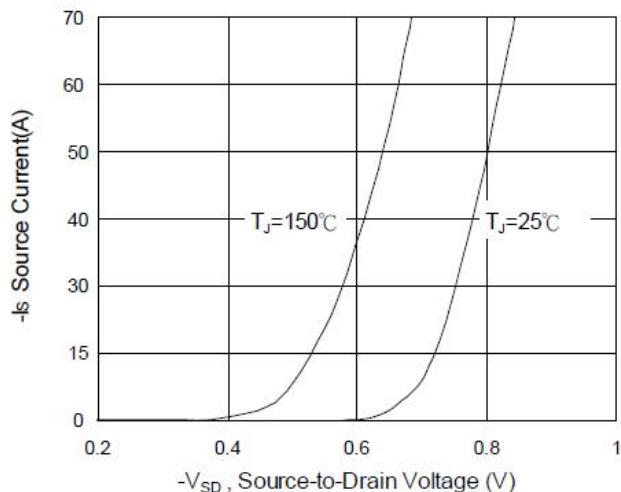


Fig.3 Source Drain Forward Characteristics

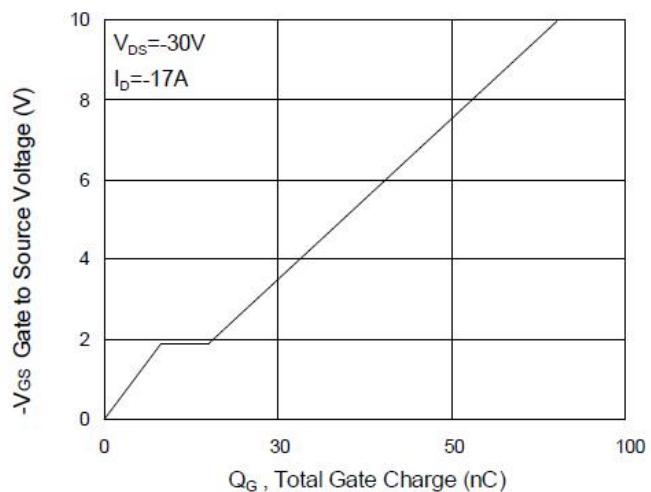


Fig.4 Gate-Charge Characteristics

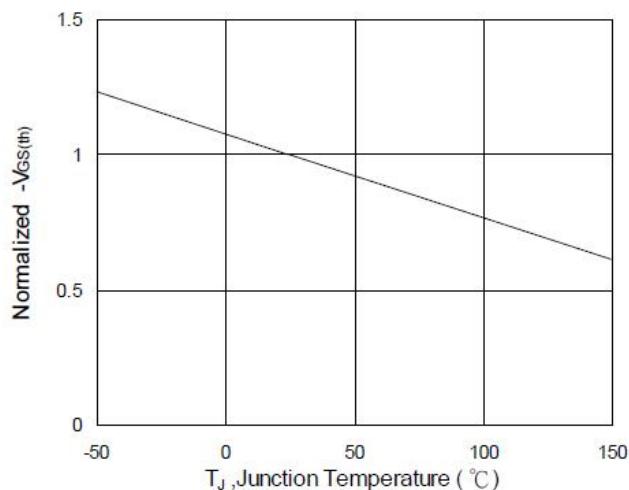


Fig.5 Normalized $V_{GS(th)}$ vs T_J

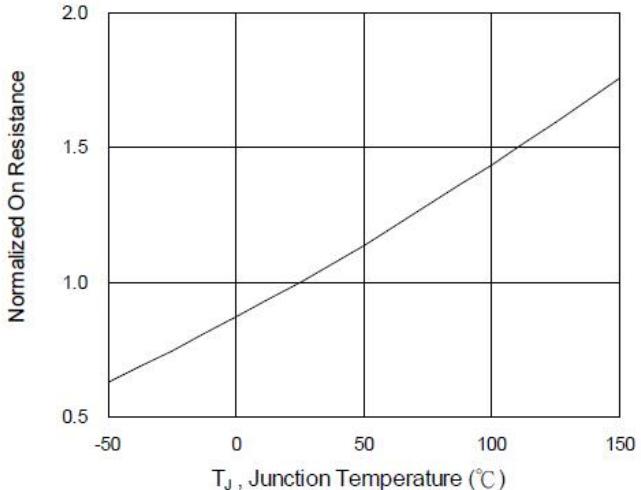


Fig.6 Normalized R_{DSON} vs T_J



P-Ch 60V Fast Switching MOSFETs

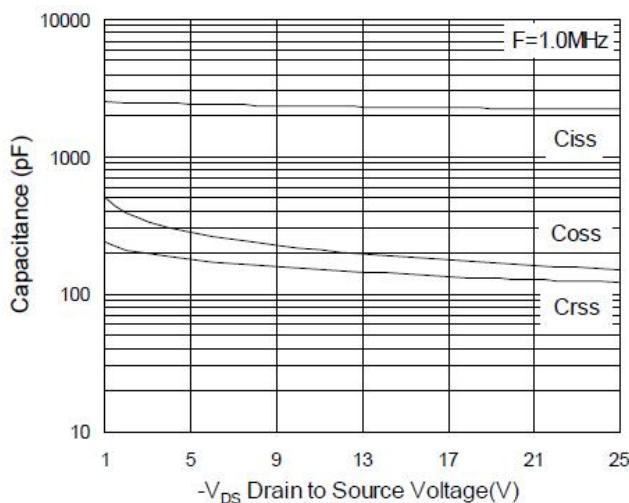


Fig.7 Capacitance

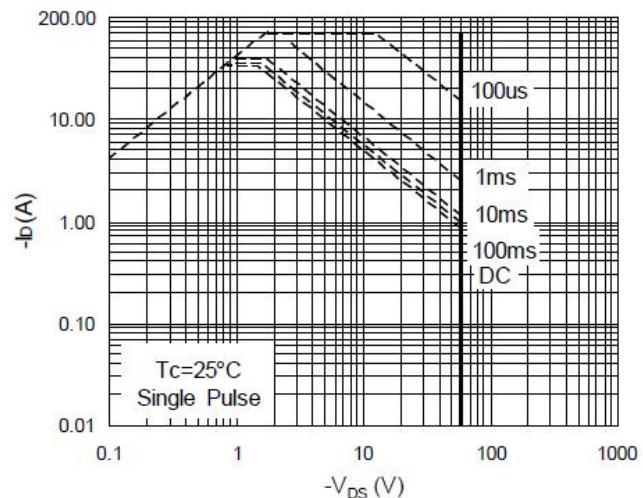


Fig.8 Safe Operating Area

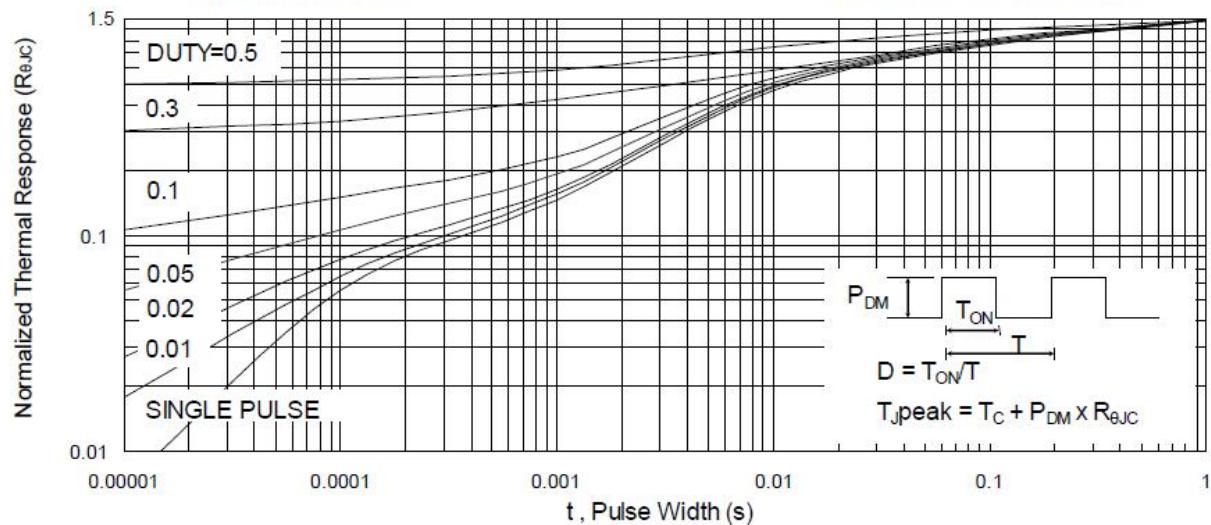


Fig.9 Normalized Maximum Transient Thermal Impedance

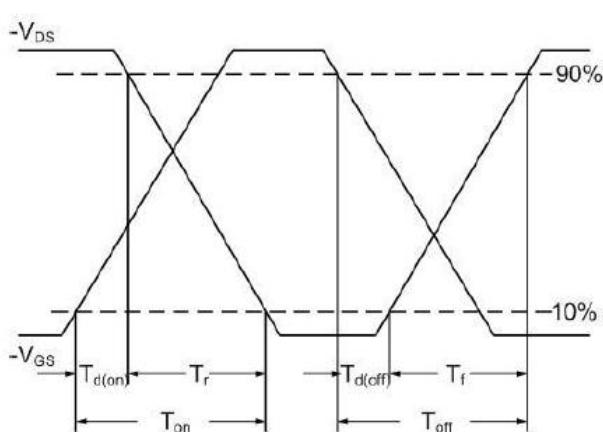


Fig.10 Switching Time Waveform

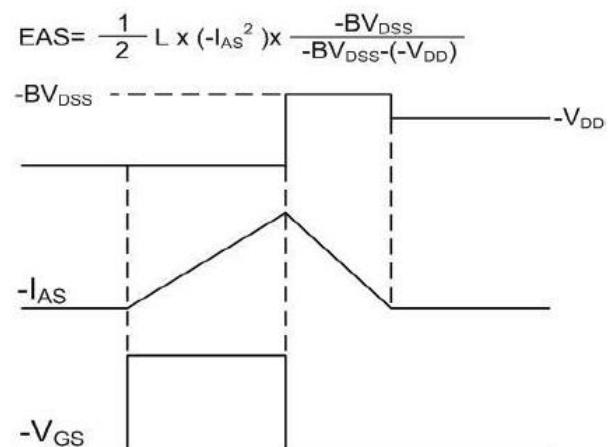


Fig.11 Unclamped Inductive Waveform



Ordering Information

Part Number	Package code	Packaging
HSM6117	SOP-8	2500/Tape&Reel

